

Notice of References Cited	Application/Control No. 10/706,610	Applicant(s)/Patent Under Reexamination SPECHT ET AL.	
	Examiner Evan Pert	Art Unit 2826	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Chaldyshev et al., "Effect of isovalent indium doping on excess arsenic in gallium arsenide grown by molecular-beam epitaxy at low temperatures", July 1998, Semiconductors, Vol. 32, No. 7, pages 692-695.
	V	Bert et al., "Enhanced arsenic excess in low-temperature grown GaAs due to indium doping", June 1997, Appl. Phys. Lett. 70 (23), pages 3146-3148.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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